

New Release

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LT8610/14/40 DC-DC CONVERTER IC STRUCTURE ANALYSIS (Techniques to reduce conduction losses)

October 5, 2016. This detailed structure analysis report examines how Linear Technology reduces conduction losses in the LT86 series third generation DC-DC converters. The LT8610/14/40 family improves ON-resistance (R_{ON}) of the MOSFET switches without increasing their die area. Each elements contributing to conduction losses (transistor, metallization, package) are identified and quantitatively analyzed in this 48-page report. The analysis of the LDMOS transistor layout and its physical construction highlights process/technology enhancements deployed in this product.

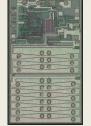












Items		DC-DC converter IC		
Product name		LT8610	LT8614	LT8640
Product introduction		Yr2010	Yr2012	Yr2013
Input voltage	V	Year3.4~42		
Max output current	А	2.5	4	5
R _{ON} (High-Side) Typ.	mΩ	120	85	67
R _{ON} (Low-Side) Typ.	mΩ	65	40	28
Max operation frequency	MHz	2.2	3	3
Package		MSOP	UDC (QFN)	UDC (QFN)

LT8610

LT8614

LT8640

Comparison table

Techniques contributing to reduction of conduction losses:

- 1. QFN package (Flip-chip, solder bumps)
- 2. Top metal layout
- 3. Bumps over transistor active areas
- 4. Reduction of specific resistance (R_{ON,SP})(*) of LDMOS

(*) $R_{ON}.sp=R_{ON}A$

Priced to sell at \$2,500

<u>Note:</u> The LT8640 has dual mode operation: Spread spectrum and Burst Mode. LETC is currently preparing circuit analysis report focusing on the implementation of spread spectrum mode.

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